

# Sub-300 fs-MIXSEL

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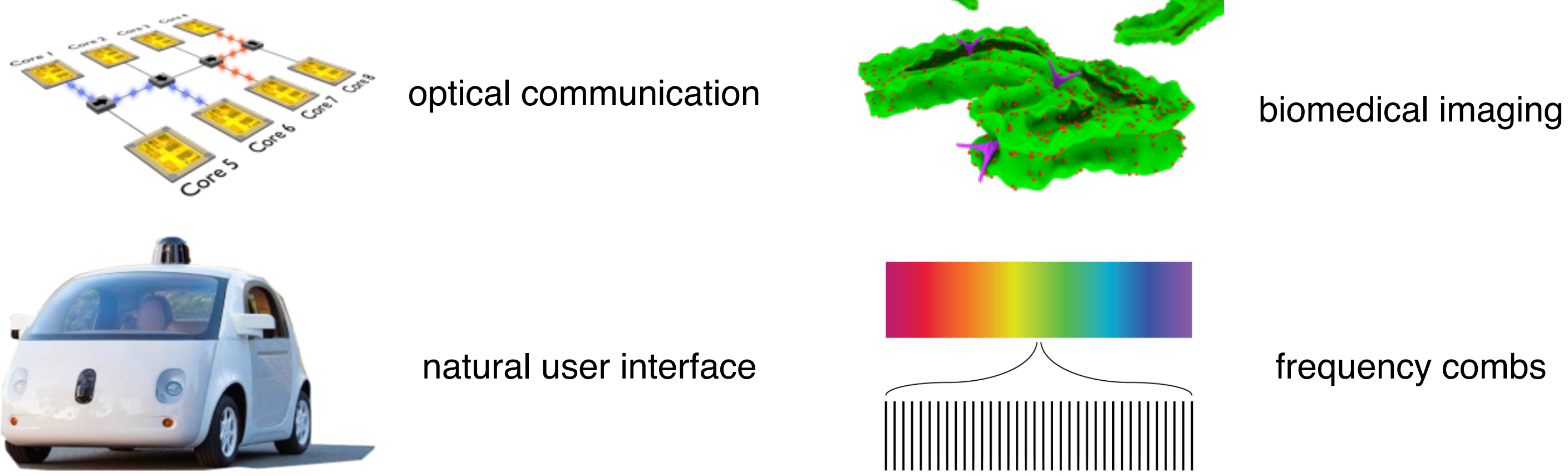
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Swiss Federal Institute of Technology Zurich

## Motivation

Potential applications of ultrafast semiconductor disk lasers (SDL)



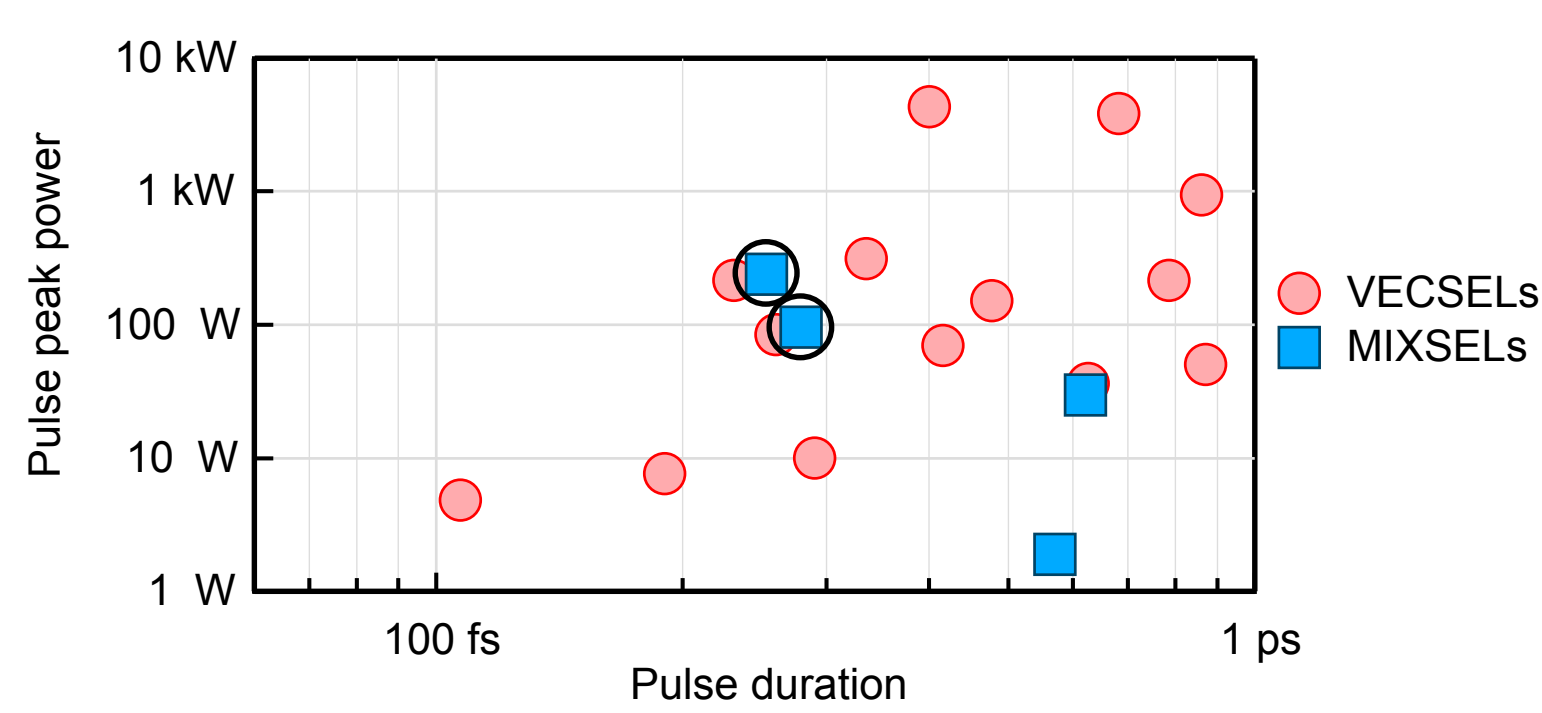
first Watt-level femtosecond VECSEL [1]

784-fs-pulses with >1 W output power in a 5.4 GHz V-cavity

first CEO-frequency detection of a SESAM-modelocked VECSEL [2]

amplified and recompressed 238-fs pulses from a 100-mW VECSEL

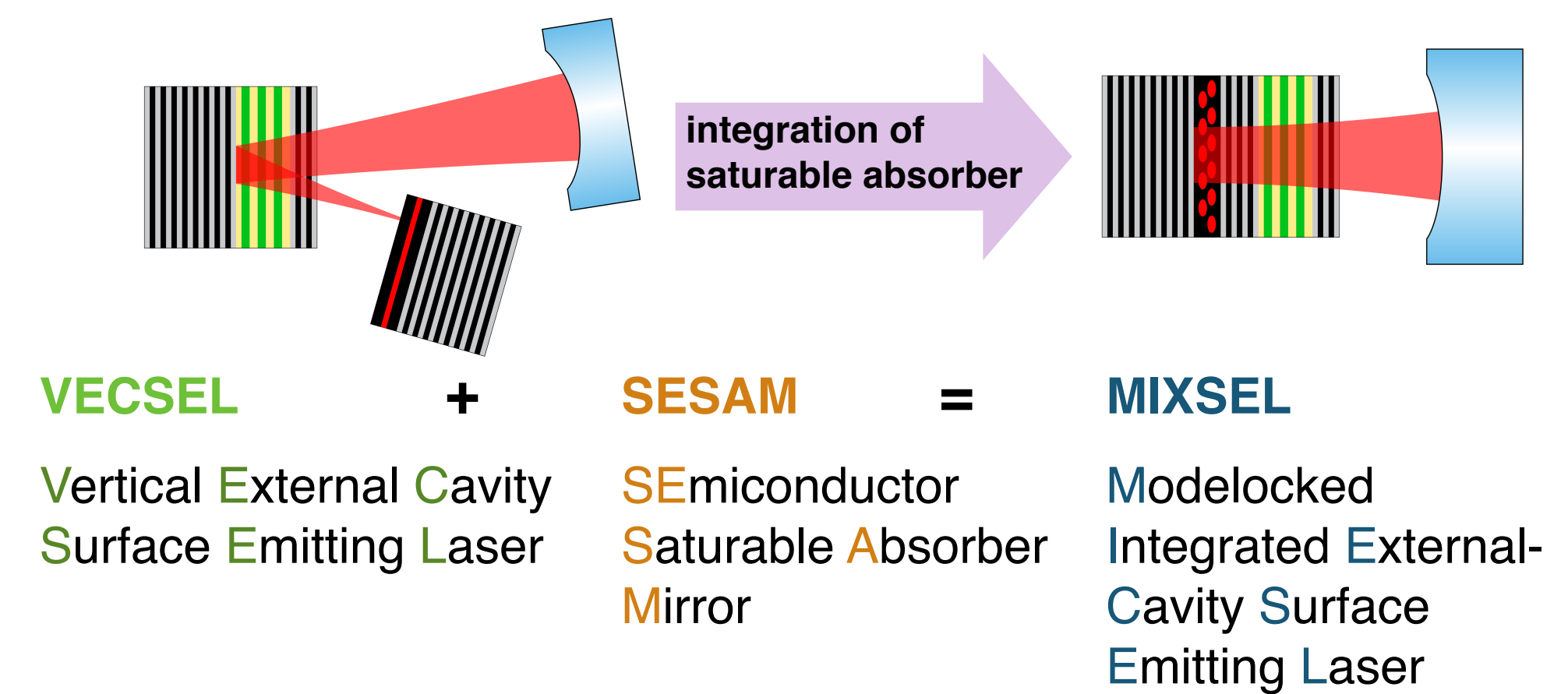
[1] M. Hoffmann et al., Optics Express (2011) vol. 19, 8108-8116  
[2] C.A. Zaugg et al., Optics Express (2014) Vol. 22, 16445-16455



Black rings indicate new results here presented

## MIXSEL concept

- semiconductor based
- integrated saturable absorber
- power scalable
- potential for monolithic design
- low noise operation



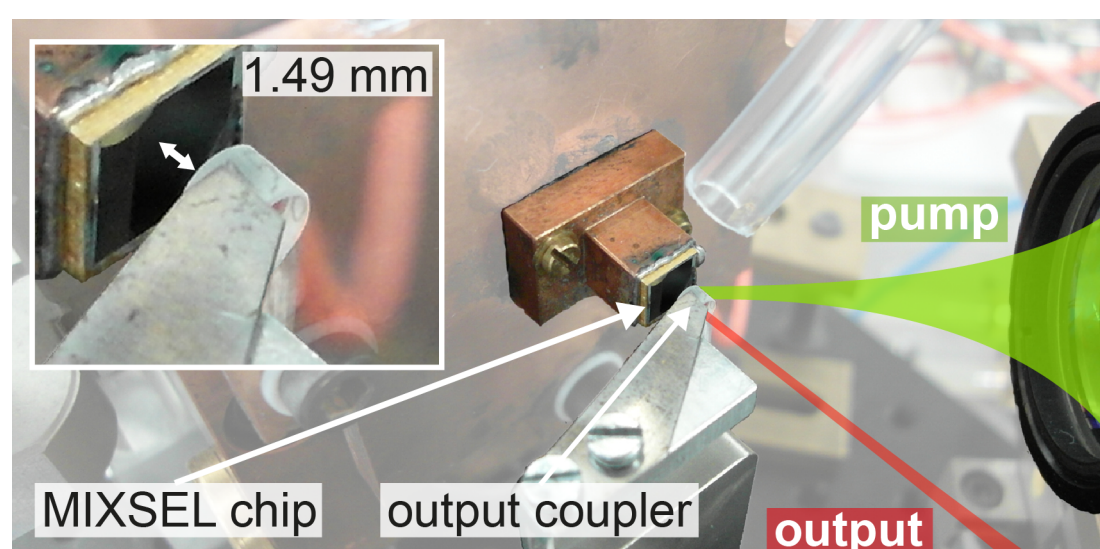
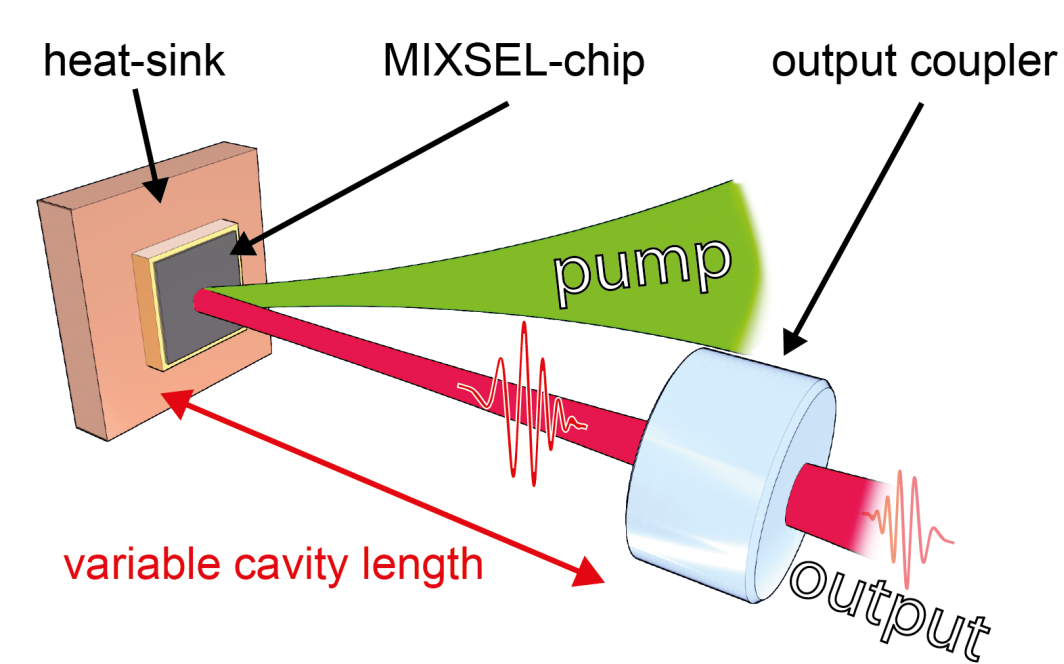
### modelocking results

28.1 ps	6.4 W	2.5 GHz	highest output power of a modelocked semiconductor laser [4]
pulse duration	output power	repetition rate	
16.9 ps	2.4 W	10 GHz	highest output power of a modelocked 10 GHz semiconductor laser [5]

[4] B. Rudin, V. J. Wittwer, D. J. H. C. Maas, M. Hoffmann, O. D. Sieber, Y. Barbarin, M. Golling, T. Südmeyer, and U. Keller, Opt. Exp. (2010) vol. 18, pp. 27582  
[5] V. J. Wittwer, M. Mangold, M. Hoffmann, O. D. Sieber, M. Golling, T. Südmeyer, U. Keller, Electronics Lett., vol. 48, No. 18, pp. 1144, 2012

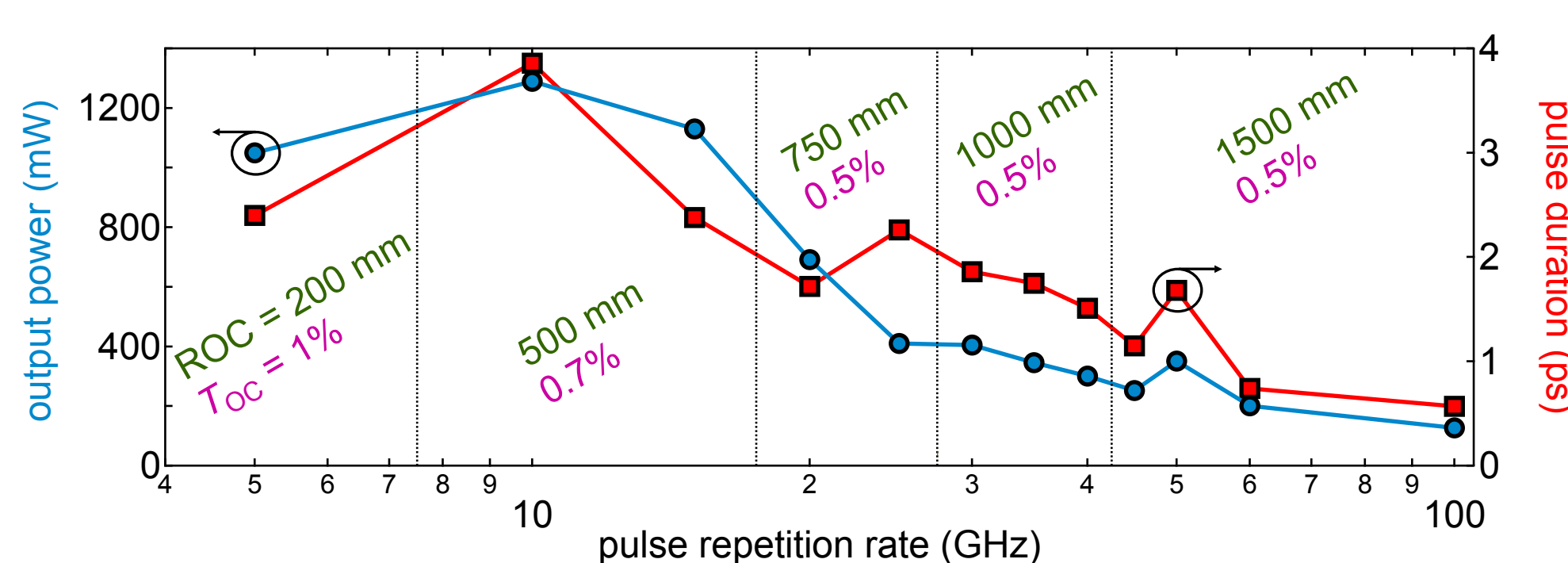
## Repetition rate scaling to 100 GHz [3]

- straight cavity for nearly arbitrarily high repetition rates
- negligible Q-switching instabilities for semiconductor gain materials
- integrated absorber: no cavity dependent mode-size difference on gain/absorber



### results of repetition rate scaling

- sub-4-ps pulses and watt-level operation up to 15 GHz
- femtosecond operation at 60 GHz and 101 GHz
- excellent beam quality:  $M^2 < 1.05$
- highest repetition rate of any fundamental mode locked SDL



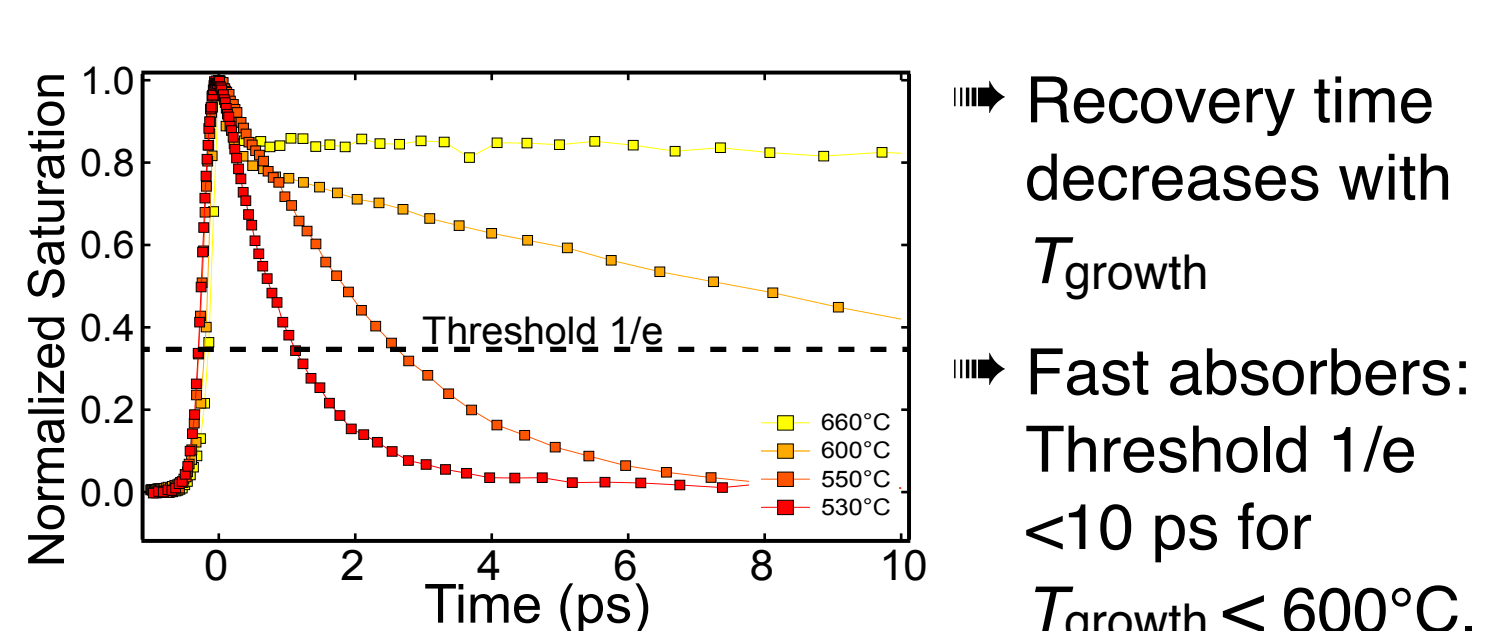
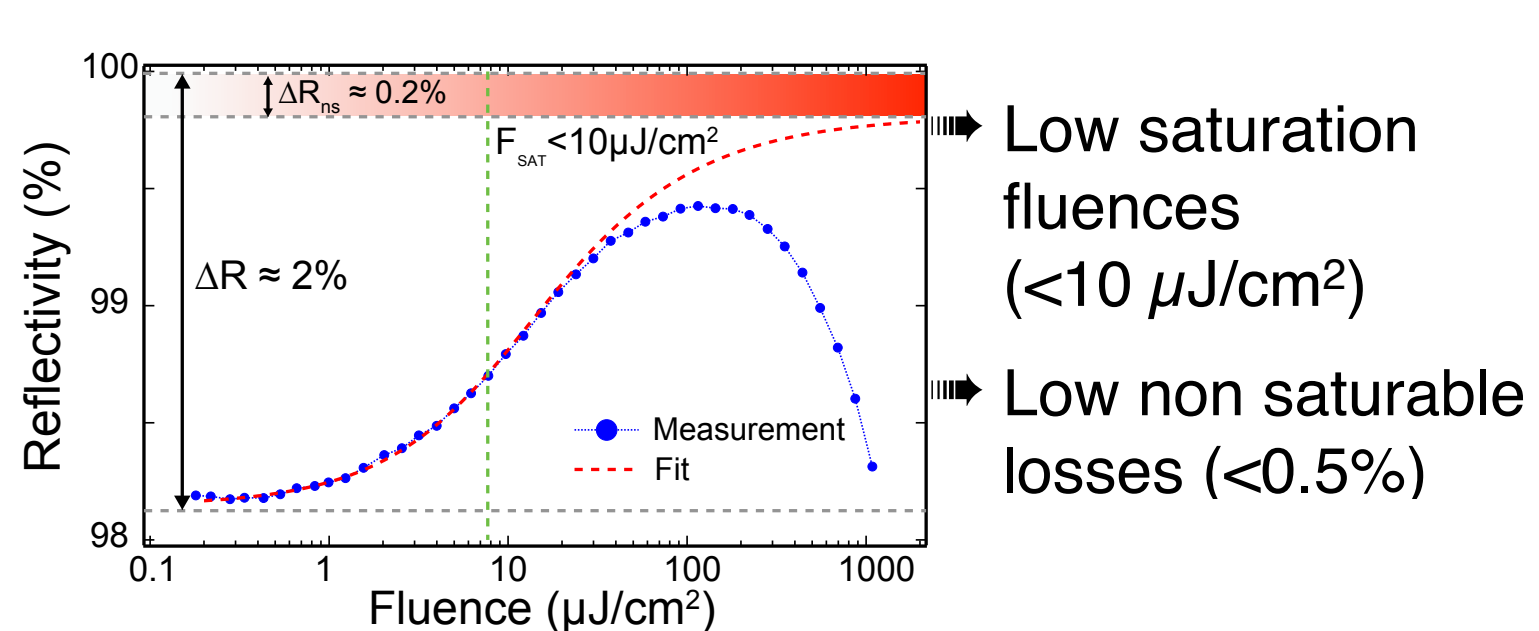
[3] M. Mangold, C. A. Zaugg, S. M. Link, M. Golling, B. W. Tilma, U. Keller, Optics Express, vol. 22, No. 5, pp. 6099-6107, 2014

## Towards an MOVPE grown MIXSEL

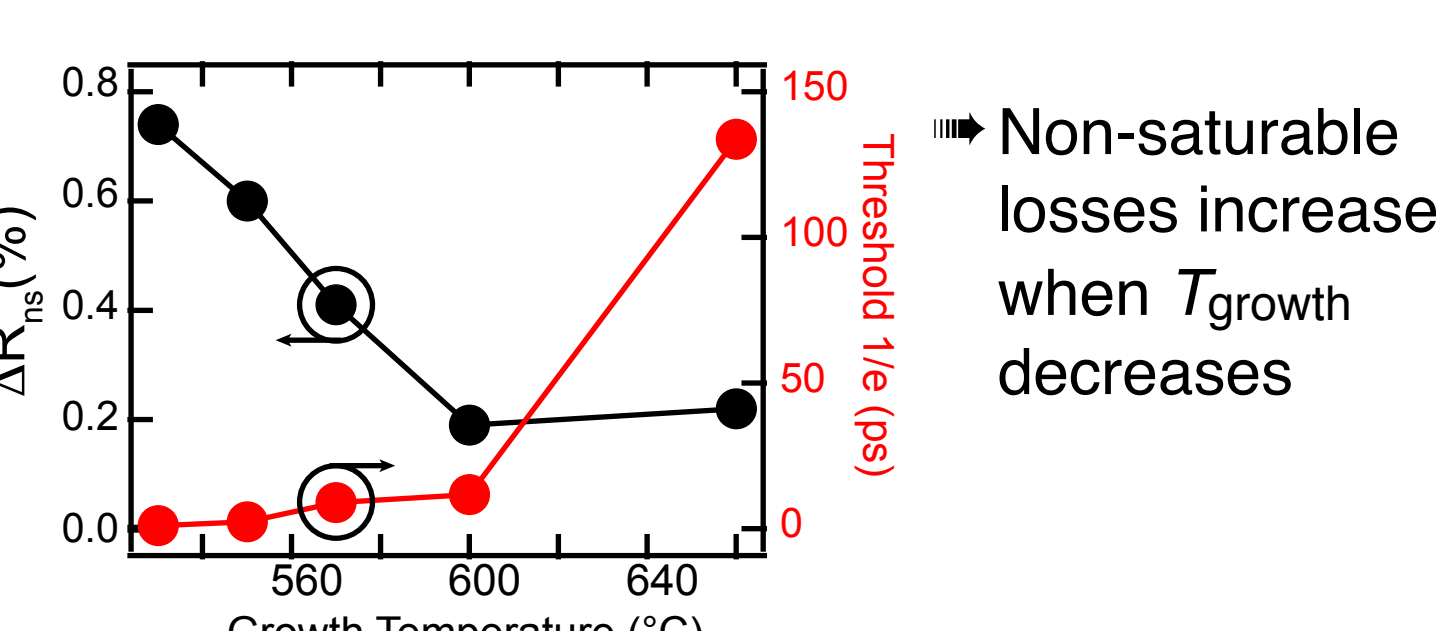
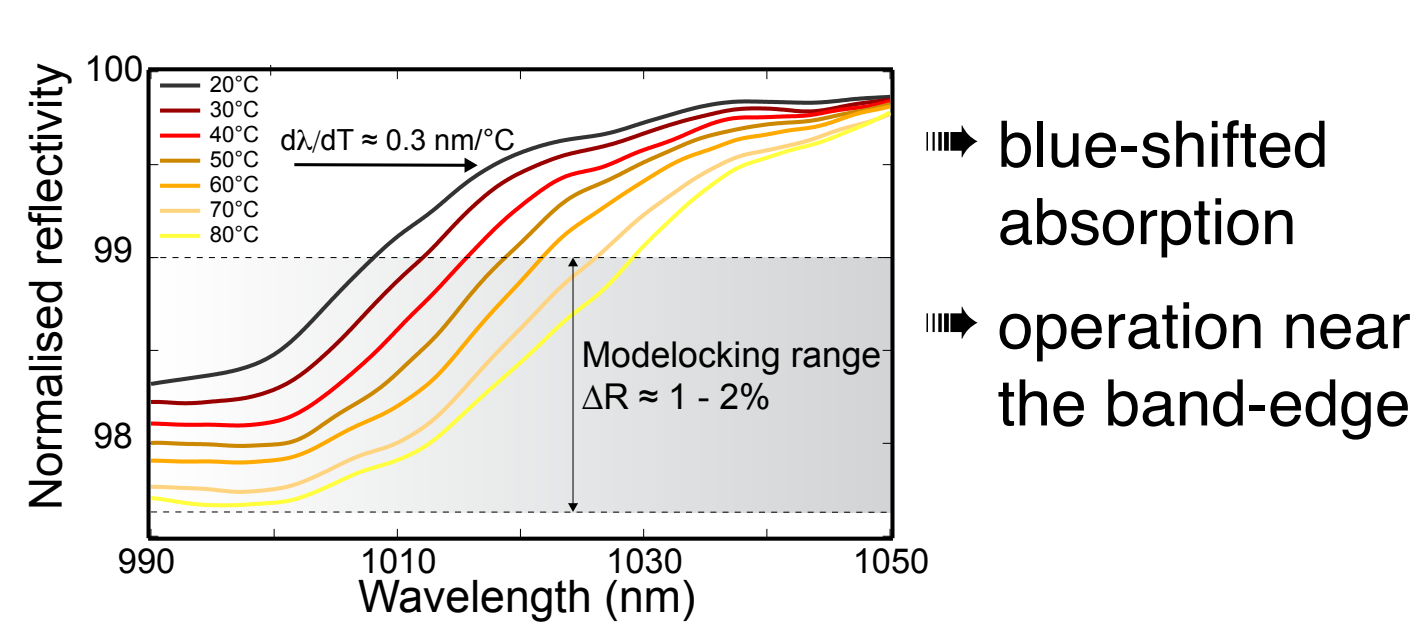
- Single MIXSEL growth run
- More uniform structure for better performances
- Industry-oriented large scale MIXSEL production

Need to optimize low temperature grown saturable absorbers from MOVPE

### MOVPE absorber characterisation



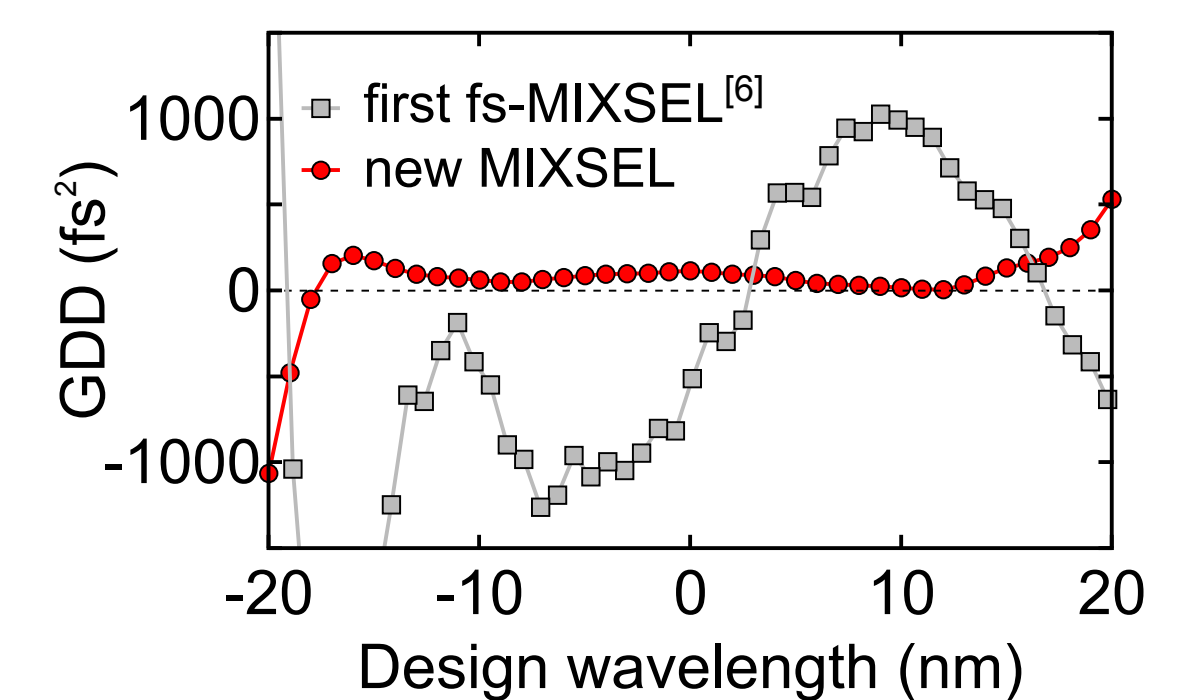
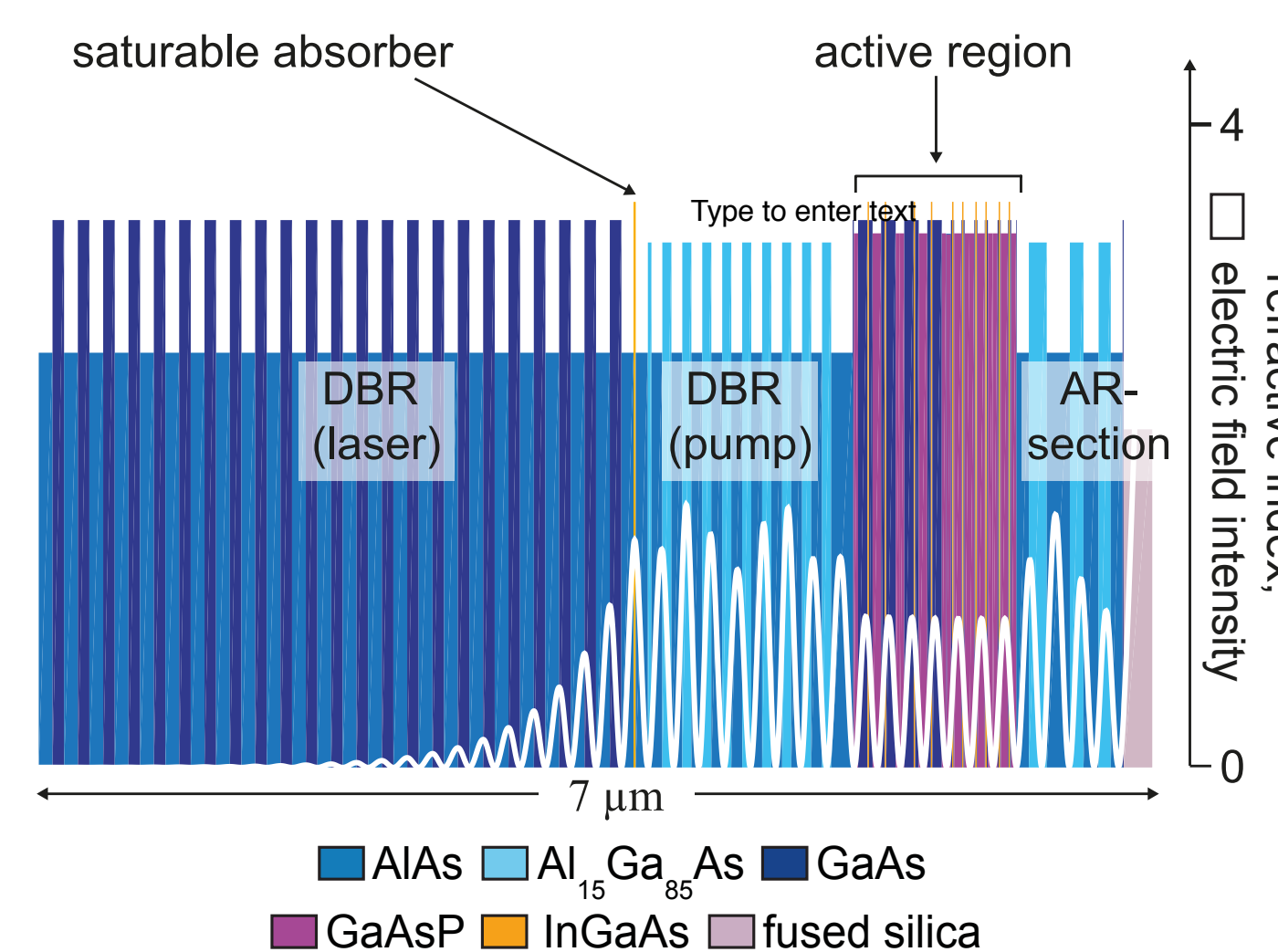
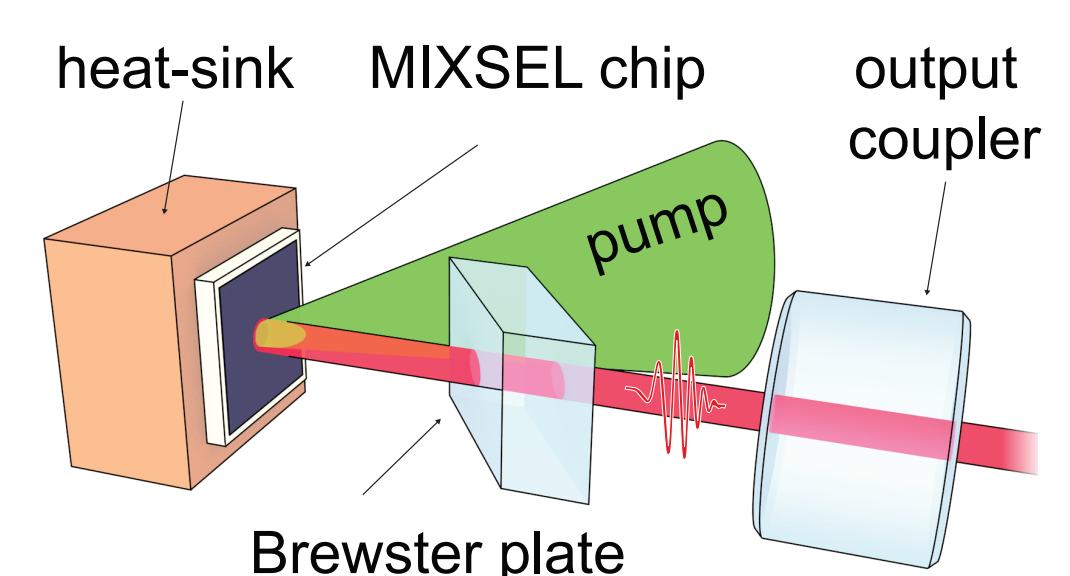
### Single quantum-well absorber



## 1040 nm - MIXSEL

### Structural improvements

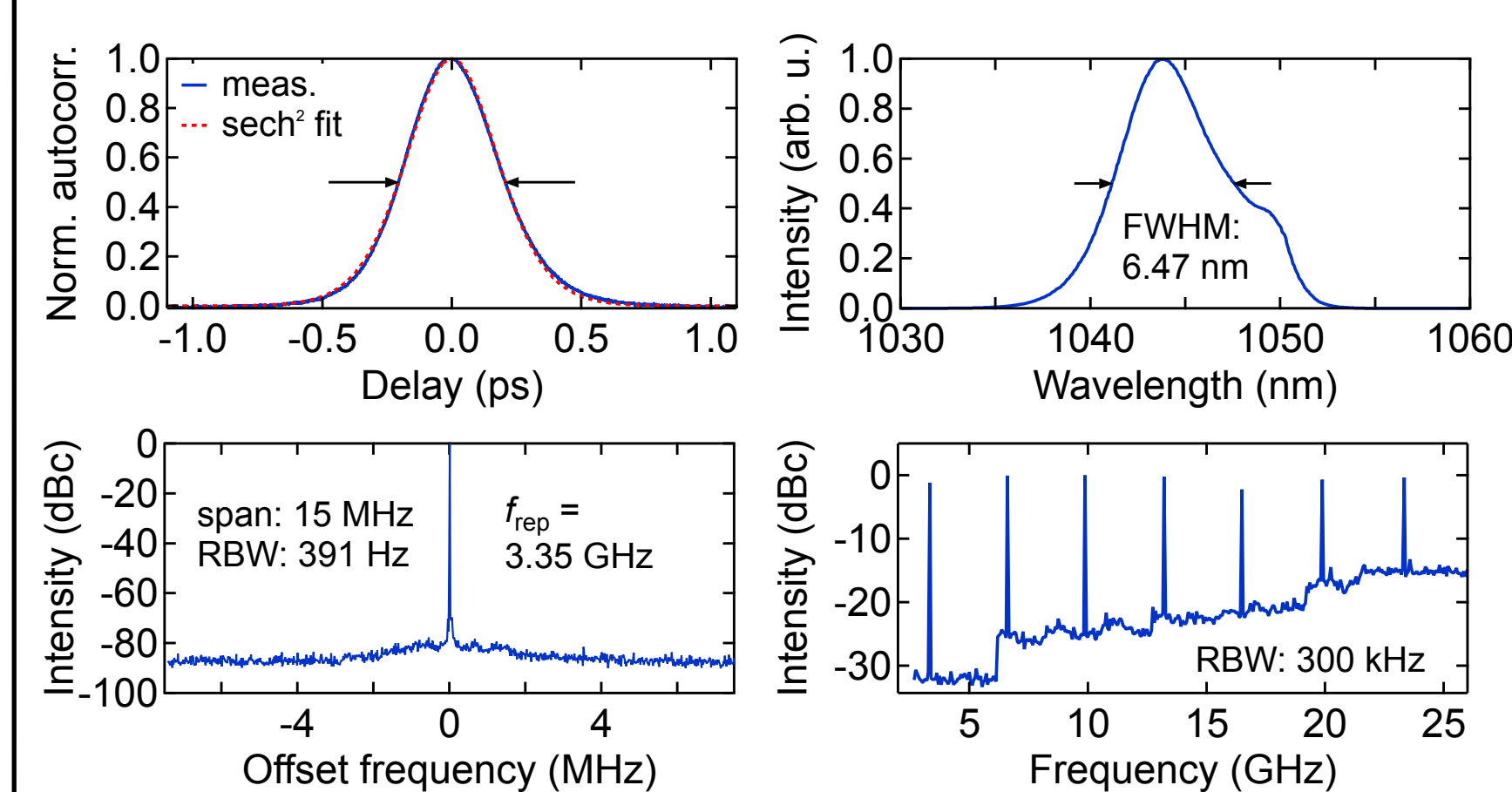
- Strain compensated active region for lasing at 1040nm
- Optimized AR section for reduced and flat dispersion
- Intracavity Brewster plate for linearly polarized laser beam



### Regrown structure:

- AR coating and active region MOVPE grown
- DBRs and absorber MBE grown

### Modelocking performance

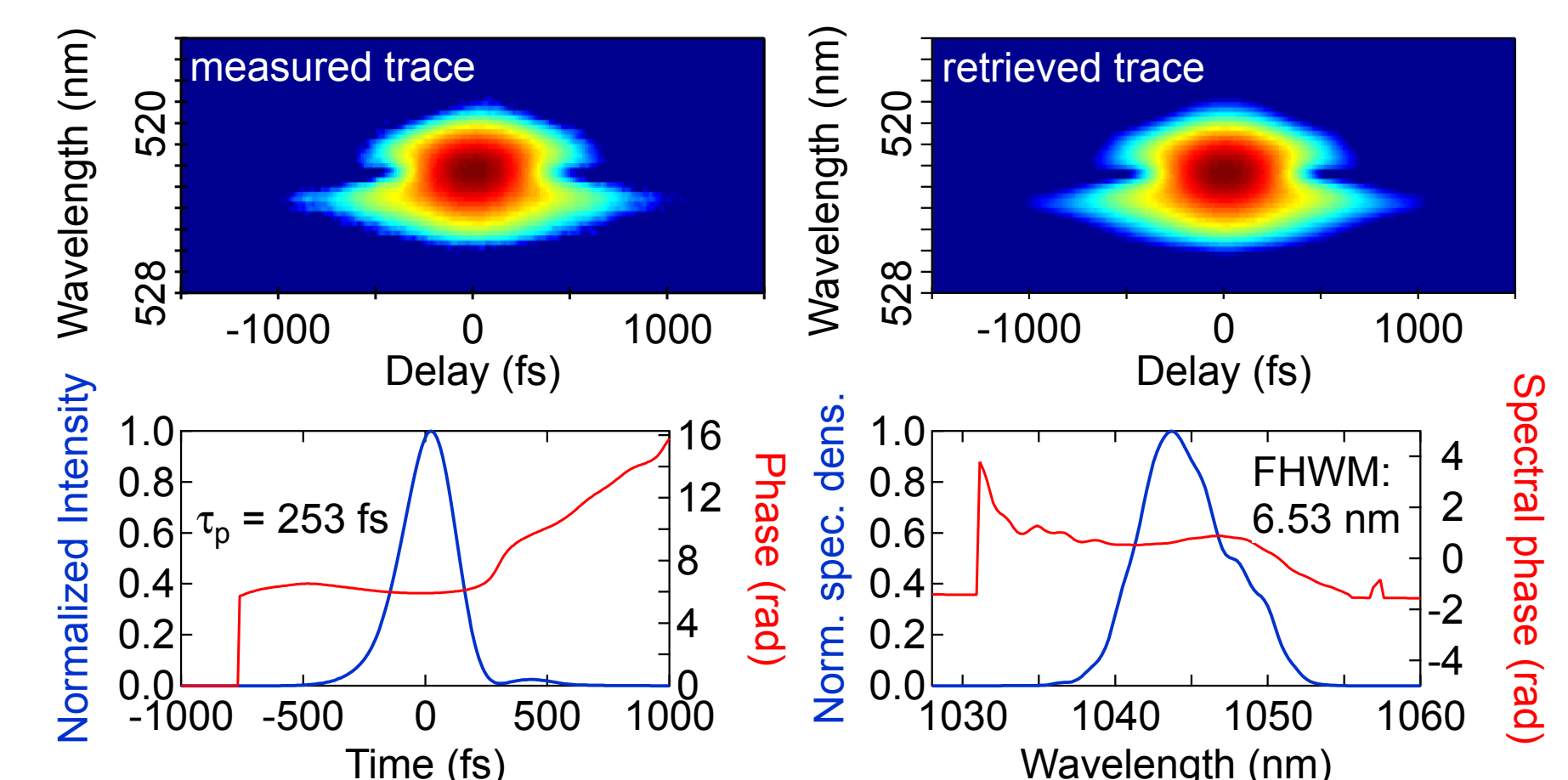


pulse duration	output power	repetition rate
253 fs	235 mW	3.35 GHz

- Shortest pulse duration from a MIXSEL (<300 fs)
- Highest peak power from a MIXSEL (>240 W)

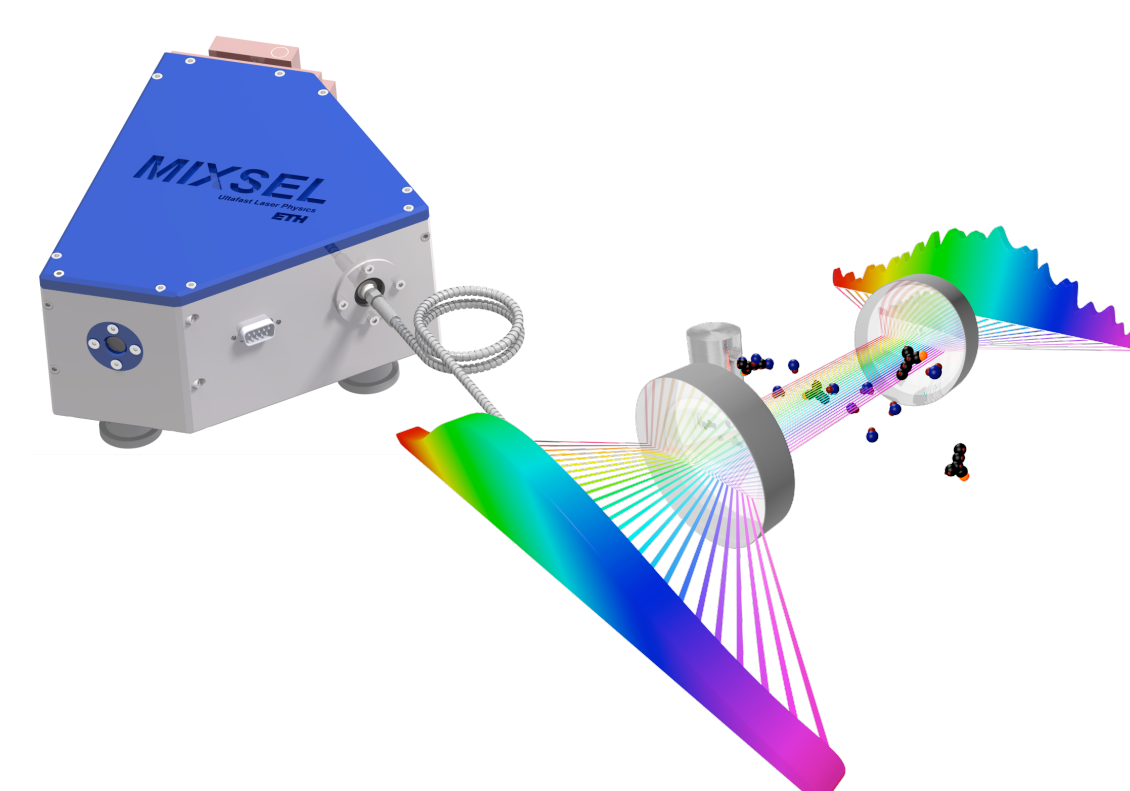
### State of the art diagnostics to confirm clean, fundamental modelocking:

- Frequency Resolved Optical Grating (FROG)
- Microwave spectrum with minimal resolution bandwidth and high SNR



[6] M. Mangold, V. J. Wittwer, C. A. Zaugg, S. M. Link, M. Golling, B. W. Tilma, and U. Keller, Opt. Express 21, 24904-24911 (2013).

## Outlook



next steps: sub-200-fs pulses with > 1W average output power from a MIXSEL

ultimate goal: fully stabilized frequency comb (repetition rate & CEO-frequency) from a compact, low cost MIXSEL